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FQP7P06 P-Channel QFET[®] MOSFET -60 V, -7 A, 410 mΩ

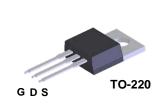
Description

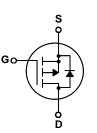
This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor®'s proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

March 2013

Features

- -7 A, -60 V, $R_{DS(on)}$ =410 m Ω (Max.) @V_{GS}=-10 V, I_D=-3.5 A
- Low Gate Charge (Typ. 6.3 nC)
- Low Crss (Typ. 25 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating





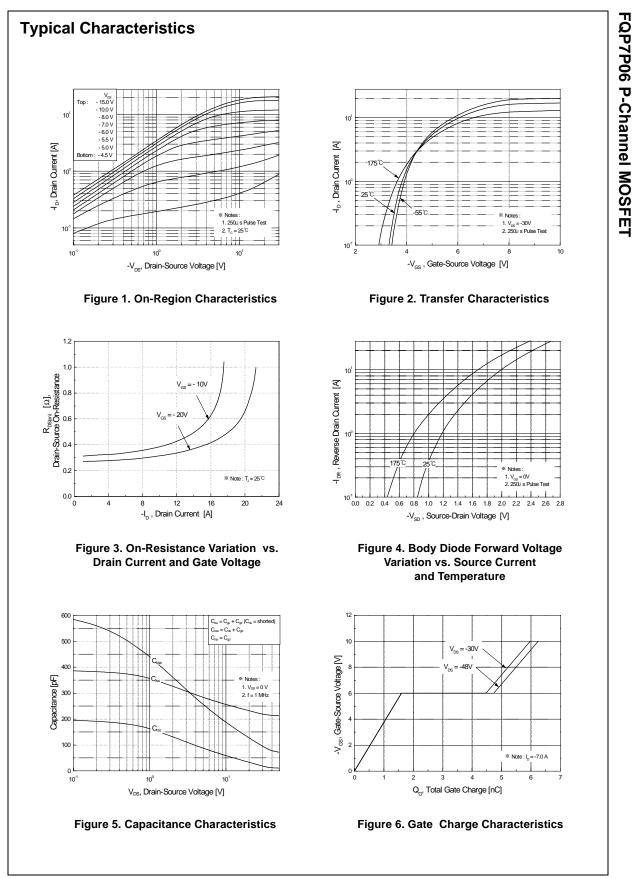
Absolute Maximum Ratings T_c = 25°C unless otherwise noted

Symbol	Parameter		FQP7P06	Unit
V _{DSS}	Drain-Source Voltage		-60	V
I _D	Drain Current - Continuous (T _C = 25°	°C)	-7.0	А
	- Continuous (T _C = 100	D°C)	-4.95	А
I _{DM}	Drain Current - Pulsed	(Note 1)	-28	А
V _{GSS}	Gate-Source Voltage		± 25	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	90	mJ
I _{AR}	Avalanche Current	(Note 1)	-7.0	А
E _{AR}	Repetitive Avalanche Energy	(Note 1)	4.5	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	-7.0	V/ns
P _D	Power Dissipation (T _C = 25°C)		45	W
	- Derate above 25°C		0.3	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C
Τ _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

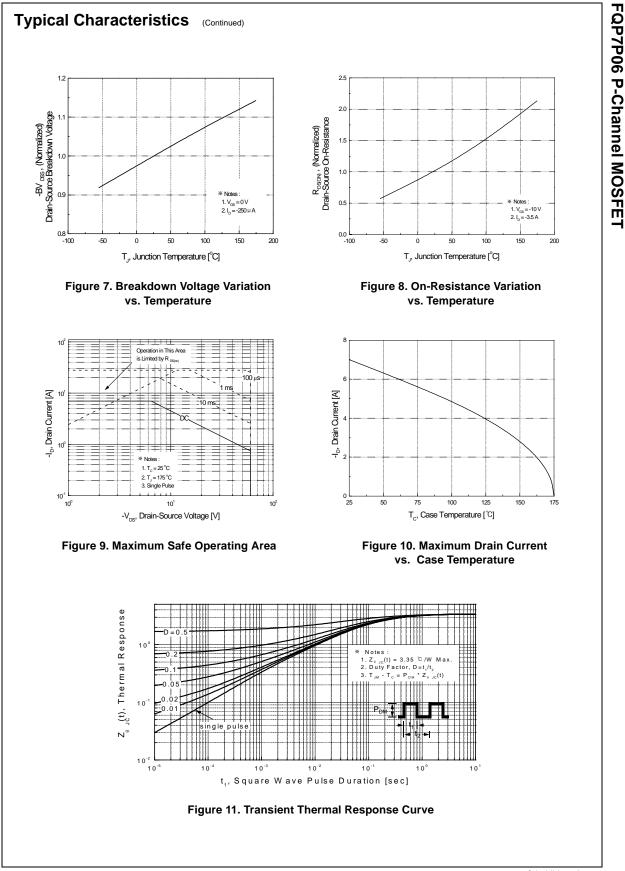
Thermal Characteristics

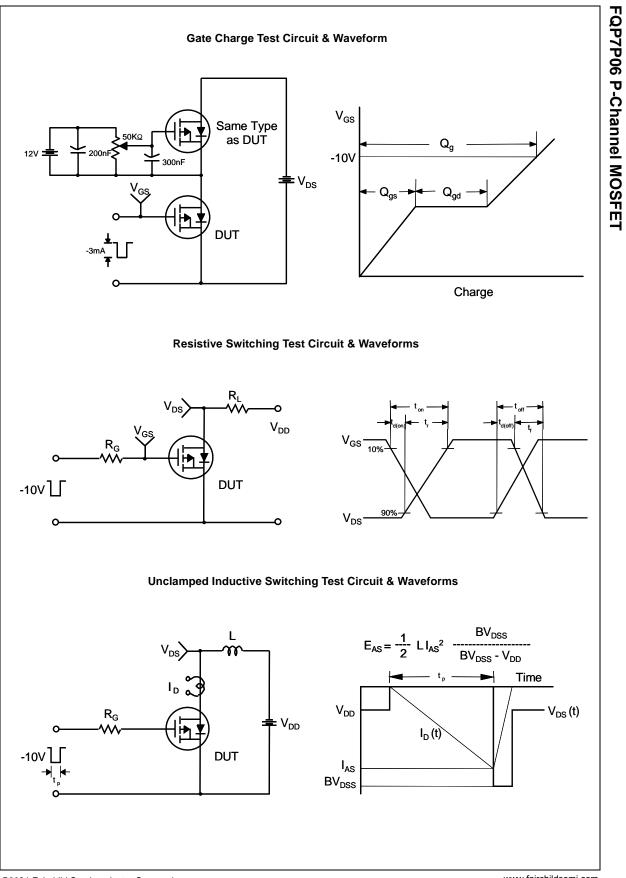
Symbol	Parameter	Тур	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case		3.35	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink	0.5		°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient		62.5	°C/W

	Test Conditions	Min	Тур	Max	Unit
racteristics					
	$V_{GS} = 0 V. I_{D} = -250 \mu A$	-60			V
Breakdown Voltage Temperature Coefficient	$I_D = -250 \mu$ A, Referenced to 25°C		-0.07		V/°C
	V _{DS} = -60 V, V _{GS} = 0 V			-1	μA
Zero Gate Voltage Drain Current $V_{DS} = -48 \text{ V}, T_C = 150^{\circ}\text{C}$				-10	μA
Gate-Body Leakage Current, Forward	$V_{GS} = -25 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$			-100	nA
Gate-Body Leakage Current, Reverse	$V_{GS} = 25 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
ractoristics					
	$V_{DS} = V_{CS}$ $ _{D} = -250 \mu A$	-2.0		-4 0	V
5		2.0		J.U	v
On-Resistance	V _{GS} = -10 V, I _D = -3.5 A		0.32	0.41	Ω
Forward Transconductance	$V_{DS} = -30 \text{ V}, \text{ I}_{D} = -3.5 \text{ A}$ (Note 4)		4.0		S
namic Characteristics			005	005	
	50 00				pF
	f = 1.0 MHz				pF
Reverse Transfer Capacitance			25	52	pF
ng Characteristics					
Turn-On Delay Time	$V_{-} = 20 V_{-} = 25 A_{-}$		7	25	ns
Turn-On Rise Time			50	110	ns
Turn-Off Delay Time	1.6 - 20 22		7.5	25	ns
Turn-Off Fall Time	(Note 4, 5)		25	60	ns
Total Gate Charge	$V_{DS} = -48 \text{ V}, I_{D} = -7.0 \text{ A},$		6.3	8.2	nC
Gate-Source Charge	V _{GS} = -10 V		1.6		nC
Gate-Drain Charge	(Note 4, 5)		3.1	1	nC
	- I Martine Dations				
	-	1	1	7.0	•
					A A
					V
,					ns
Reverse Recovery Charge			0.23		μC
ting : Pulse width limited by maximum junction temper $_{S} = -7.0A$, $V_{DD} = -25V$, $R_{G} = 25 \Omega$, Starting $T_{J} = 25^{\circ}C$ di/dt $\leq 300A/\mu_{S}$, $V_{DD} \leq BV_{DSS}$, Starting $T_{J} = 25^{\circ}C$	rature		0.20		pro
Pulse width \leq 300 μ s, Duty cycle \leq 2% dependent of operating temperature					
	Drain-Source Breakdown Voltage Breakdown Voltage Temperature Coefficient Zero Gate Voltage Drain Current Gate-Body Leakage Current, Forward Gate-Body Leakage Current, Reverse acteristics Gate Threshold Voltage Static Drain-Source On-Resistance Forward Transconductance Characteristics Input Capacitance Output Capacitance Reverse Transfer Capacitance 1 (Characteristics) Turn-On Delay Time Turn-On Delay Time Turn-Off Delay Time Turn-Off Fall Time Total Gate Charge Gate-Source Charge Gate-Source Charge Gate-Drain Charge Durce Diode Characteristics an Maximum Continuous Drain-Source Diode Reverse Recovery Time Reverse Recovery Time Reverse Recovery Charge	Drain-Source Breakdown Voltage $V_{GS} = 0 V, I_D = -250 \mu A$ Breakdown Voltage Temperature Coefficient $I_D = -250 \mu A$, Referenced to 25°CZero Gate Voltage Drain Current $V_{DS} = -60 V, V_{GS} = 0 V$ VDS = -60 V, Vacs = 0 V $V_{DS} = -48 V, T_C = 150°C$ Gate-Body Leakage Current, Forward $V_{GS} = -25 V, V_{DS} = 0 V$ Gate-Body Leakage Current, Reverse $V_{GS} = 25 V, V_{DS} = 0 V$ Gate Threshold Voltage $V_{DS} = V_{GS}, I_D = -250 \mu A$ Static Drain-Source $V_{GS} = -10 V, I_D = -3.5 A$ Forward Transconductance $V_{DS} = -30 V, I_D = -3.5 A$ Forward Transconductance $V_{DS} = -30 V, I_D = -3.5 A$ Input Capacitance $V_{DS} = -25 V, V_{GS} = 0 V,$ characteristics $I_{DD} = -30 V, I_D = -3.5 A,$ Input Capacitance $V_{DS} = -25 V, V_{GS} = 0 V,$ characteristics $I_{DD} = -30 V, I_D = -3.5 A,$ Input Capacitance $V_{DS} = -25 Q, V_{GS} = 0 V,$ characteristics $I_{DD} = -30 V, I_D = -3.5 A,$ Turn-On Delay Time $V_{DD} = -30 V, I_D = -3.5 A,$ Turn-Off Delay Time $V_{DS} = -48 V, I_D = -7.0 A,$ Gate-Drain Charge $V_{GS} = -10 V$ Gate-Drain Charge $V_{GS} = -10 V$ Maximum Pulsed Drain-Source Diode Forward CurrentMaximum Pulsed Drain-Source Diode Forward CurrentMaximum Pulsed Drain-Source Diode Forward CurrentMaximum Pulsed Drain-Source Diode Forward CurrentDrain-Source Diode Forward Voltage $V_{GS} = 0 V, I_S = -7.0 A,$ Reverse Recovery Time $V_{GS} = 0 V, I_S = -7.0 A,$ <td>Drain-Source Breakdown Voltage$V_{GS} = 0 V, I_D = -250 \mu A$-60Breakdown Voltage Temperature Coefficient$I_D = -250 \mu A, Referenced to 25^{\circ}C$Zero Gate Voltage Drain Current$V_{DS} = -60 V, V_{GS} = 0 V$Gate-Body Leakage Current, Forward$V_{CS} = -25 V, V_{DS} = 0 V$Gate-Body Leakage Current, Reverse$V_{GS} = 25 V, V_{DS} = 0 V$Gate-Body Leakage Current, Reverse$V_{GS} = -25 V, V_{DS} = 0 V$acteristics$V_{GS} = -10 V, I_D = -3.5 A$Gate Threshold Voltage$V_{DS} = -30 V, I_D = -3.5 A$Forward Transconductance$V_{DS} = -30 V, I_D = -3.5 A$Forward Transconductance$V_{DS} = -25 V, V_{GS} = 0 V,$CharacteristicsInput Capacitance$V_{DS} = -30 V, I_D = -3.5 A,$Turn-On Delay TimeTurn-On Rise Time$R_G = 25 \Omega$Turn-Off Fall Time(Note 4, 5)Turn-Off Fall TimeTurn-Off State Charge$V_{DS} = -48 V, I_D = -7.0 A,$Gate-Source ChargeV_{DS} = -10 VGate-Source ChargeV_{GS} = 0 V, I_S = -7.0 A,Maximum Continuous Drain-Source Diode Forward CurrentMaximum Pulsed Drain-Source Diode Forward CurrentMaximum Pulsed Drain-Source Diode Forward CurrentGate-Source Chode Forward Voltage$V_{GS} = 0 V, I_S = -7.0 A,$Reverse Recovery Time$V_$</td> <td>$\begin{array}{c c c c c c c } \hline Drain-Source Breakdown Voltage V_{GS} = 0 V, I_D = -250 \ \mu A & -60 & \\ \hline I_D = -250 \ \mu A, Referenced to 25^{\circ}C & & -0.07 \\ \hline V_{DS} = -60 \ V, V_{GS} = 0 \ V & & \\ \hline V_{DS} = -48 \ V, T_C = 150^{\circ}C & & \\ \hline Cate-Body Leakage Current, Forward V_{GS} = -25 \ V, V_{DS} = 0 \ V & & \\ \hline Cate-Body Leakage Current, Reverse V_{GS} = 25 \ V, V_{DS} = 0 \ V & & \\ \hline acteristics \\ \hline Gate Threshold Voltage V_{DS} = V_{GS}, I_D = -250 \ \mu A & -2.0 & \\ \hline acteristics \\ \hline Gate Threshold Voltage V_{DS} = -10 \ V, I_D = -3.5 \ A & & 0.32 \\ \hline On-Resistance V_{DS} = -30 \ V, I_D = -3.5 \ A & (Note 4) & & 4.0 \\ \hline Characteristics \\ \hline Input Capacitance V_{DS} = -30 \ V, I_D = -3.5 \ A & (Note 4) & & 225 \\ \hline output Capacitance for each end end end end end end end end end end$</td> <td>$\begin{array}{c c c c c c c c c c c c c c c c c c c$</td>	Drain-Source Breakdown Voltage $V_{GS} = 0 V, I_D = -250 \mu A$ -60Breakdown Voltage Temperature Coefficient $I_D = -250 \mu A, Referenced to 25^{\circ}C$ Zero Gate Voltage Drain Current $V_{DS} = -60 V, V_{GS} = 0 V$ Gate-Body Leakage Current, Forward $V_{CS} = -25 V, V_{DS} = 0 V$ Gate-Body Leakage Current, Reverse $V_{GS} = 25 V, V_{DS} = 0 V$ Gate-Body Leakage Current, Reverse $V_{GS} = -25 V, V_{DS} = 0 V$ acteristics $V_{GS} = -10 V, I_D = -3.5 A$ Gate Threshold Voltage $V_{DS} = -30 V, I_D = -3.5 A$ Forward Transconductance $V_{DS} = -30 V, I_D = -3.5 A$ Forward Transconductance $V_{DS} = -25 V, V_{GS} = 0 V,$ CharacteristicsInput Capacitance $V_{DS} = -30 V, I_D = -3.5 A,$ Turn-On Delay TimeTurn-On Rise Time $R_G = 25 \Omega$ Turn-Off Fall Time(Note 4, 5)Turn-Off Fall TimeTurn-Off State Charge $V_{DS} = 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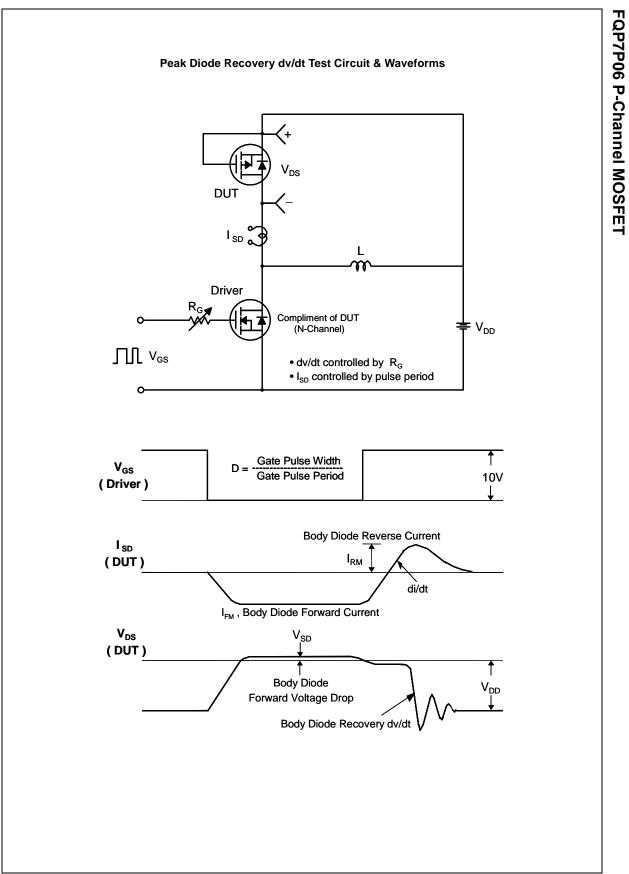
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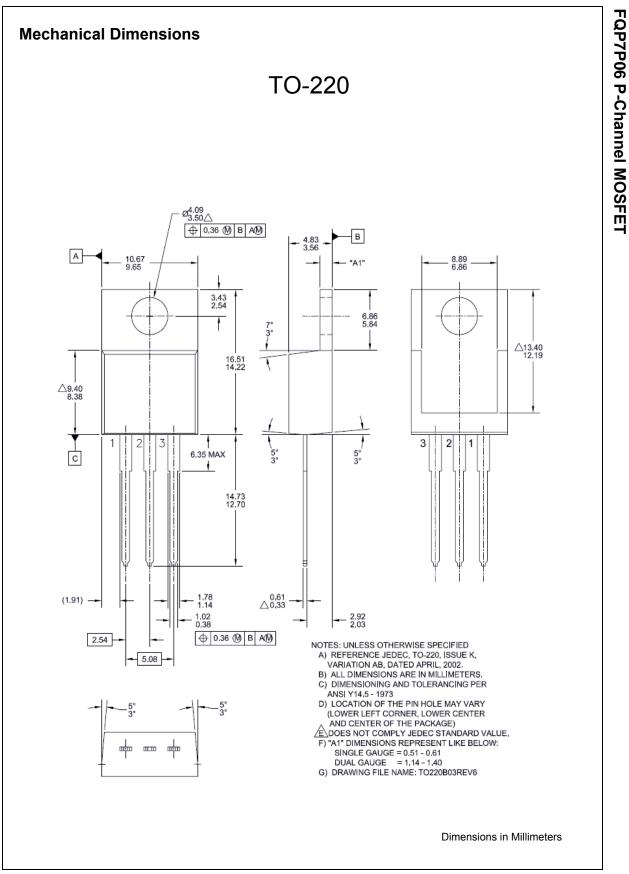




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